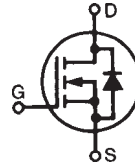
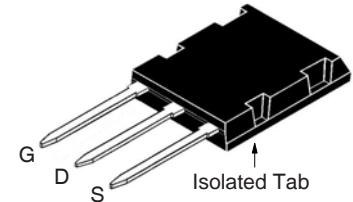


**Polar3™ HiPerFET™
Power MOSFET**
IXFL132N50P3
(Electrically Isolated Tab)

 N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Rectifier

$$\begin{aligned} V_{DSS} &= 500V \\ I_{D25} &= 63A \\ R_{DS(on)} &\leq 43m\Omega \\ t_{rr} &\leq 250ns \end{aligned}$$

ISOPLUS264


 G = Gate D = Drain
S = Source

| Symbol | Test Conditions | Maximum Ratings | |
|---------------|--|-----------------|------------------|
| V_{DSS} | $T_J = 25^\circ\text{C to } 150^\circ\text{C}$ | 500 | V |
| V_{DGR} | $T_J = 25^\circ\text{C to } 150^\circ\text{C}, R_{GS} = 1M\Omega$ | 500 | V |
| V_{GSS} | Continuous | ± 30 | V |
| V_{GSM} | Transient | ± 40 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ | 63 | A |
| I_{DM} | $T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM} | 330 | A |
| I_A | $T_C = 25^\circ\text{C}$ | 66 | A |
| E_{AS} | $T_C = 25^\circ\text{C}$ | 3 | J |
| dv/dt | $I_S \leq I_{DM}, V_{DD} \leq V_{DSS}, T_J \leq 150^\circ\text{C}$ | 35 | V/ns |
| P_D | $T_C = 25^\circ\text{C}$ | 520 | W |
| T_J | | -55 ... +150 | $^\circ\text{C}$ |
| T_{JM} | | 150 | $^\circ\text{C}$ |
| T_{stg} | | -55 ... +150 | $^\circ\text{C}$ |
| T_L | 1.6mm (0.062 in.) from Case for 10s | 300 | $^\circ\text{C}$ |
| T_{SOLD} | Plastic Body for 10s | 260 | $^\circ\text{C}$ |
| F_C | Mounting Force | 40..120 / 9..27 | N/lb. |
| V_{ISOL} | 50/60 Hz, RMS $t = 1 \text{ min}$ | 2500 | V~ |
| | $I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$ | 3000 | V~ |
| Weight | | 8 | g |

Features

- Silicon Chip on Direct-Copper-Bond Substrate
 - High Power Dissipation
 - Isolated Mounting Surface
 - 2500V Electrical Isolation
- Avalanche Rated
- Low Package Inductance
- Fast Intrinsic Rectifier
- Low $R_{DS(on)}$ and Q_G

Advantages

- Easy to Mount
- Space Savings

Applications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- Uninterrupted Power Supplies
- AC Motor Drives
- High Speed Power Switching Applications

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|--------------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V, I_D = 3mA$ | 500 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 8mA$ | 3.0 | | 5.0 V |
| I_{GSS} | $V_{GS} = \pm 30V, V_{DS} = 0V$ | | | $\pm 200 \text{ nA}$ |
| I_{DSS} | $V_{DS} = V_{DSS}, V_{GS} = 0V$ $T_J = 125^\circ\text{C}$ | | | 50 μA 6 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V, I_D = 66A$, Note 1 | | | 43 m Ω |

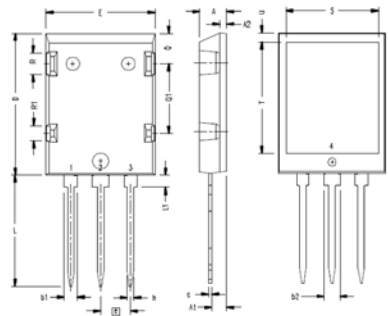
| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|------------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 10\text{V}, I_D = 66\text{A}$, Note 1 | 68 | 115 | S |
| C_{iss} | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$ | | 18.6 | nF |
| C_{oss} | | | 1750 | pF |
| C_{rss} | | | 5.0 | pF |
| R_{Gi} | Gate Input Resistance | | 1.0 | Ω |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 66\text{A}$ $R_G = 1\Omega$ (External) | | 44 | ns |
| t_r | | | 9 | ns |
| $t_{d(off)}$ | | | 72 | ns |
| t_f | | | 8 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 66\text{A}$ | | 250 | nC |
| Q_{gs} | | | 90 | nC |
| Q_{gd} | | | 52 | nC |
| R_{thJC} | | | | 0.24°C/W |
| R_{thCS} | | 0.15 | | $^\circ\text{C/W}$ |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values | | |
|----------|---|-----------------------|------|---------------|
| | | Min. | Typ. | Max. |
| I_s | $V_{GS} = 0\text{V}$ | | | 132 A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | 530 A |
| V_{SD} | $I_F = 100\text{A}, V_{GS} = 0\text{V}$, Note 1 | | | 1.5 V |
| t_{rr} | $I_F = 66\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$ | | | 250 ns |
| Q_{RM} | | | 1.9 | μC |
| I_{RM} | | | 16.4 | A |

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

ISOPLUS264 (IXFL) OUTLINE



1 = Gate
2,4 = Drain
3 = Source

| SYM | INCHES | | MILLIMETERS | |
|-----|----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .190 | .205 | 4.83 | 5.21 |
| A1 | .102 | .118 | 2.59 | 3.00 |
| A2 | .046 | .055 | 1.17 | 1.40 |
| b | .045 | .055 | 1.14 | 1.40 |
| b1 | .087 | .102 | 2.21 | 2.59 |
| b2 | .111 | .126 | 2.82 | 3.20 |
| c | .020 | .029 | 0.51 | 0.74 |
| D | 1.020 | 1.040 | 25.91 | 26.42 |
| E | .770 | .799 | 19.56 | 20.29 |
| e | .215 BSC | | 5.46 BSC | |
| L | .780 | .820 | 19.81 | 20.83 |
| L1 | .080 | .102 | 2.03 | 2.59 |
| Q | .210 | .235 | 5.33 | 5.97 |
| Q1 | .490 | .513 | 12.45 | 13.03 |
| R | .150 | .180 | 3.81 | 4.57 |
| R1 | .100 | .130 | 2.54 | 3.30 |
| S | .668 | .690 | 16.97 | 17.53 |
| T | .801 | .821 | 20.34 | 20.85 |
| U | .065 | .080 | 1.65 | 2.03 |

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| | 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

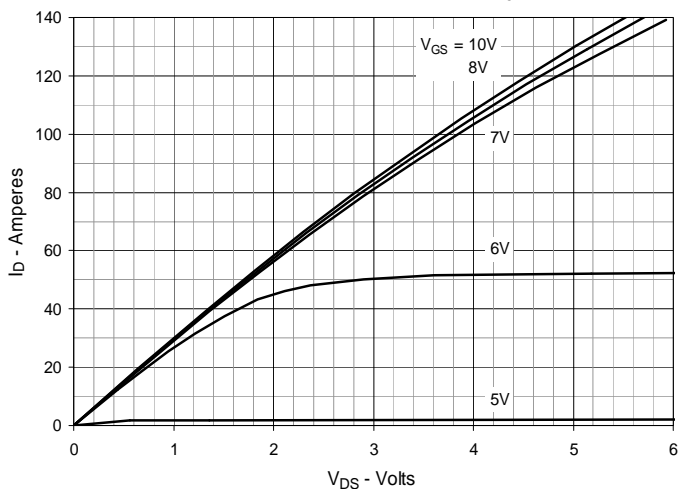
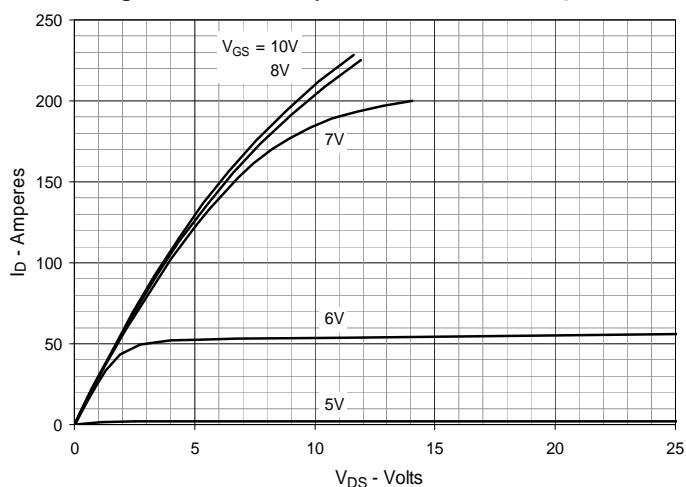
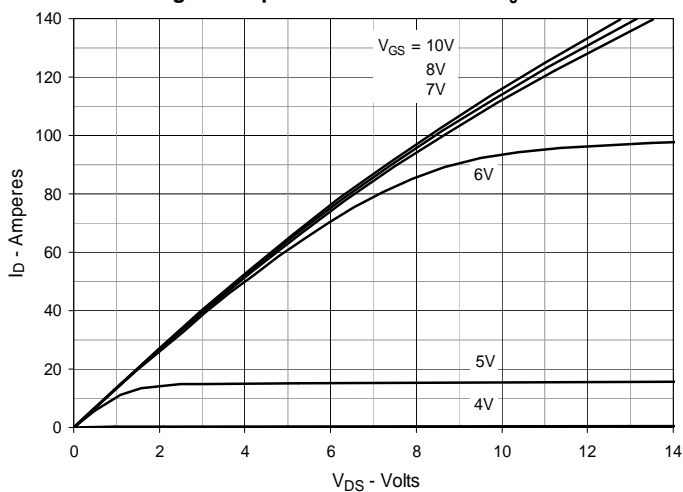
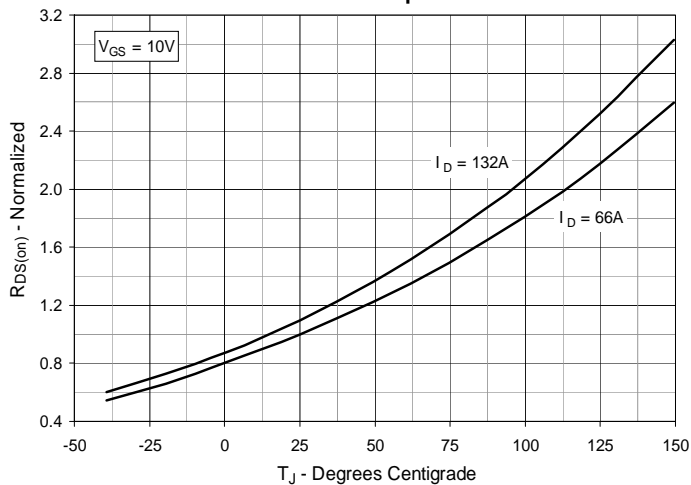
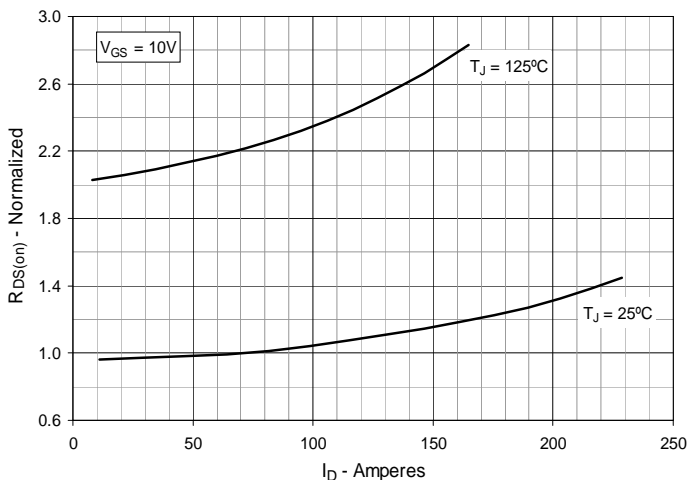
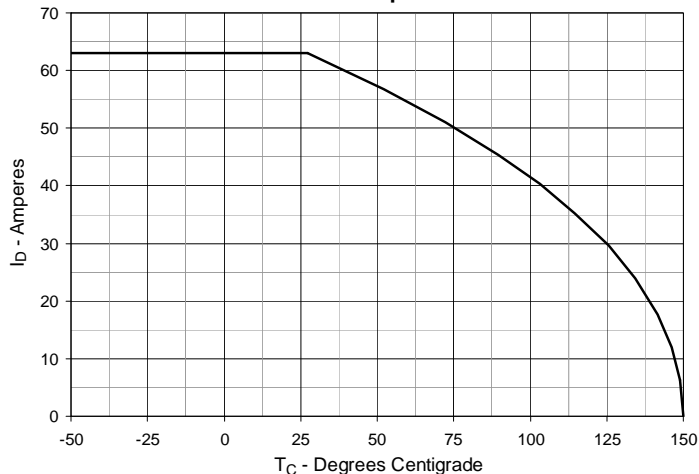
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 66\text{A}$ Value vs. Junction Temperature

Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 66\text{A}$ Value vs. Drain Current

Fig. 6. Maximum Drain Current vs. Case Temperature


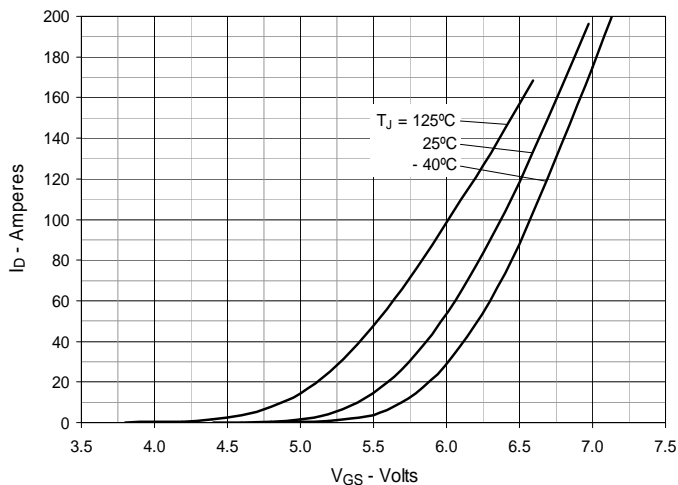
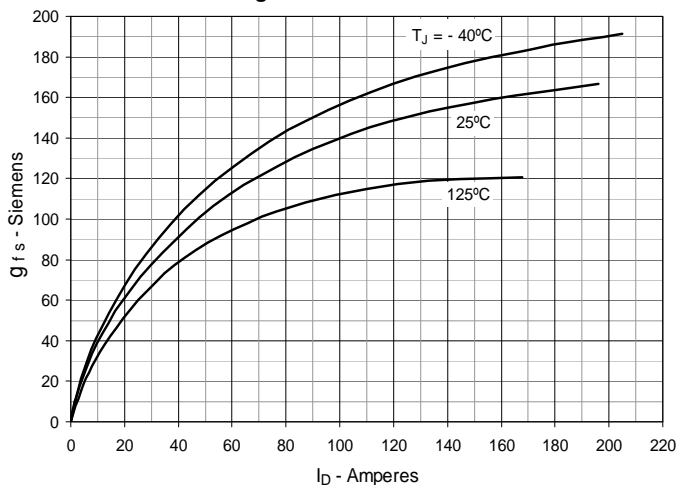
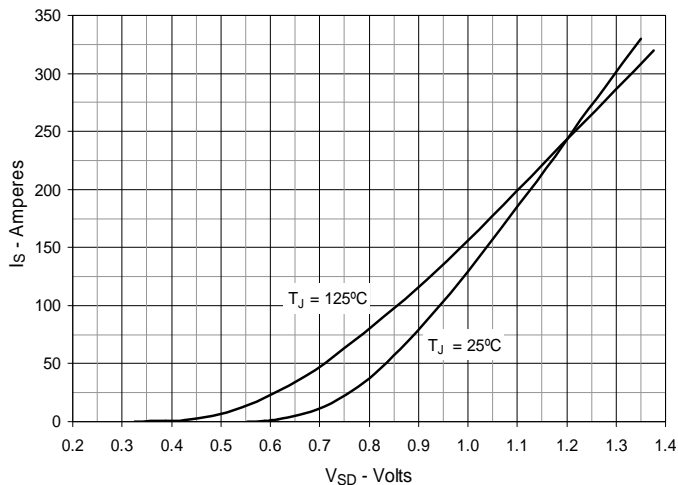
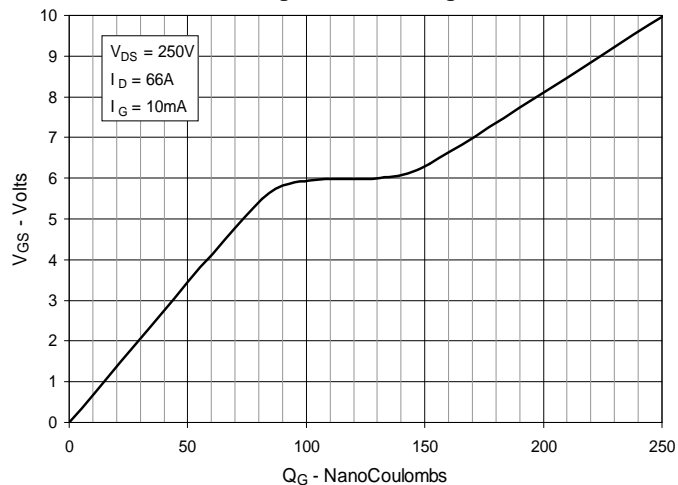
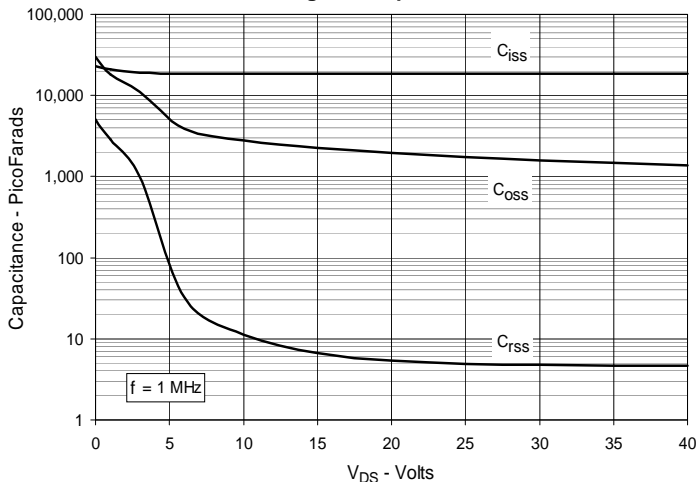
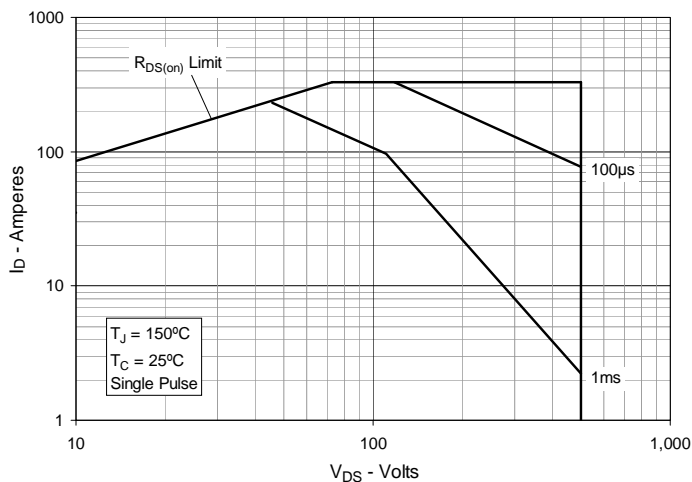
Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Forward-Bias Safe Operating Area


Fig. 13. Maximum Transient Thermal Impedance

